

ABSTRACT

An object of the present invention is to provide a polishing pad excellent in polishing rate and superior in longevity without generating center slow. Another object of the present invention is to provide a method of manufacturing a semiconductor device with the polishing pad. Disclosed is a polishing pad having a polishing layer consisting of a polyurethane foam having fine cells, wherein a high-molecular-weight polyol component that is a starting component of the polyurethane foam contains a hydrophobic high-molecular-weight polyol A having a number-average molecular weight of 550 to 800 and a hydrophobic high-molecular-weight polyol B having a number-average molecular weight of 950 to 1300 in an A/B ratio of from 10/90 to 50/50 by weight.